


FS50VSJ-3

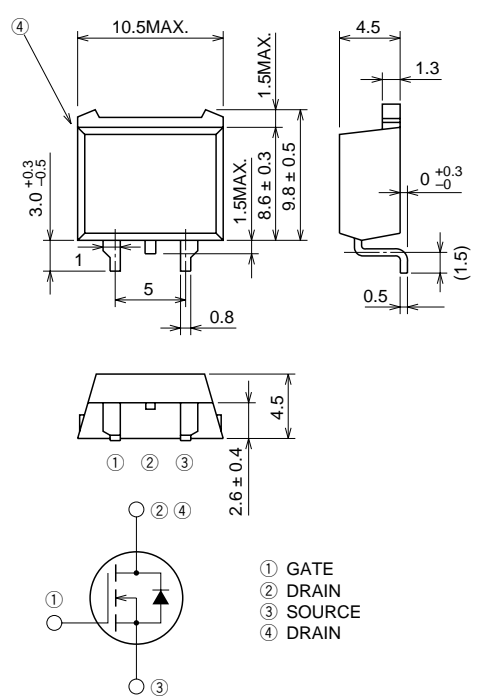
HIGH-SPEED SWITCHING USE

FS50VSJ-3



- 4V DRIVE
- V_{DSS} 150V
- $r_{DS(ON)}$ (MAX)30m Ω
- I_D 50A
- Integrated Fast Recovery Diode (TYP.)125ns

OUTLINE DRAWING Dimensions in mm



① GATE
② DRAIN
③ SOURCE
④ DRAIN

TO-220S

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

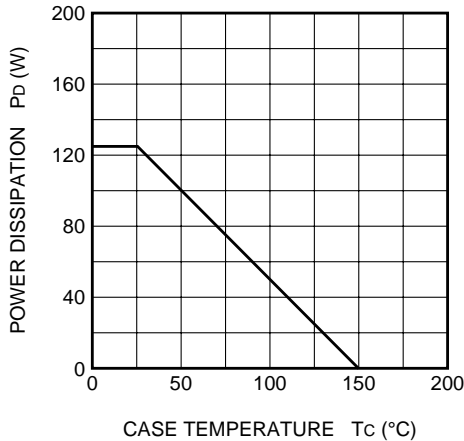
Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	150	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		50	A
I_{DM}	Drain current (Pulsed)		200	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu H$	50	A
I_S	Source current		50	A
I_{SM}	Source current (Pulsed)		200	A
P_D	Maximum power dissipation		125	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	1.2	g

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

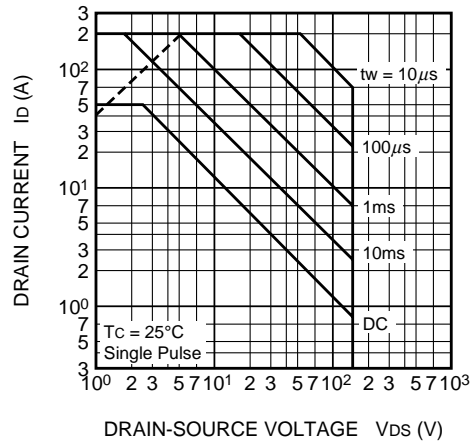
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	150	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±20V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 150V, V _{GS} = 0V	—	—	0.1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	1.0	1.5	2.0	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 25A, V _{GS} = 10V	—	23	30	mΩ
r _{DS} (ON)	Drain-source on-state resistance	I _D = 25A, V _{GS} = 4V	—	24	32	mΩ
V _{DS} (ON)	Drain-source on-state voltage	I _D = 25A, V _{GS} = 10V	—	0.58	0.75	V
y _{fs}	Forward transfer admittance	I _D = 25A, V _{DS} = 10V	—	62	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	8200	—	pF
C _{oss}	Output capacitance		—	870	—	pF
C _{rss}	Reverse transfer capacitance		—	440	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 80V, I _D = 25A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	54	—	ns
t _r	Rise time		—	110	—	ns
t _d (off)	Turn-off delay time		—	850	—	ns
t _f	Fall time		—	340	—	ns
V _{SD}	Source-drain voltage		I _S = 25A, V _{GS} = 0V	—	1.0	1.5
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	1.00	°C/W
t _{rr}	Reverse recovery time	I _S = 50A, di _s /dt = -100A/μs	—	125	—	ns

PERFORMANCE CURVES

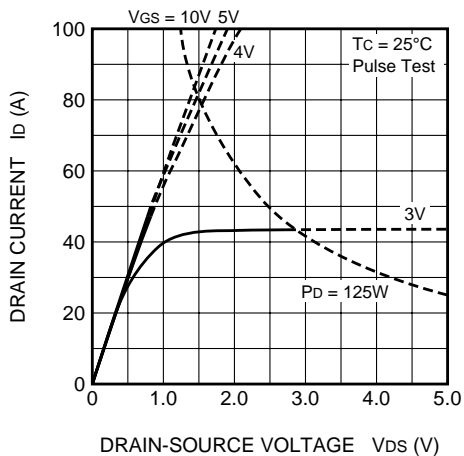
POWER DISSIPATION DERATING CURVE



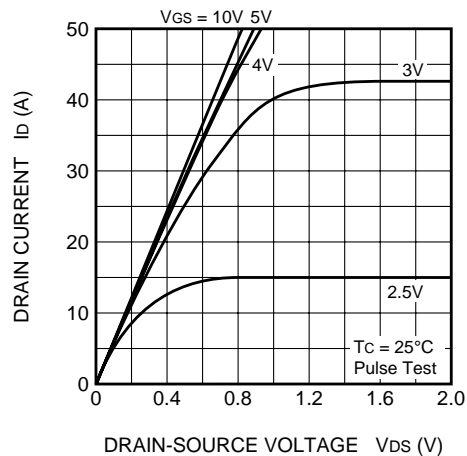
MAXIMUM SAFE OPERATING AREA

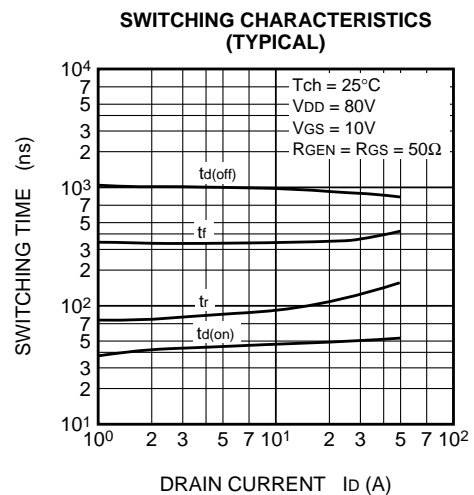
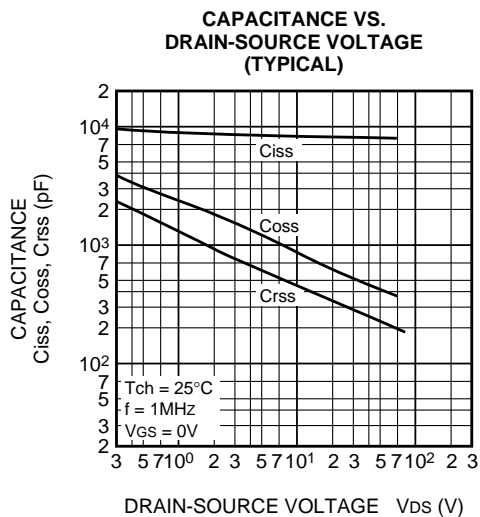
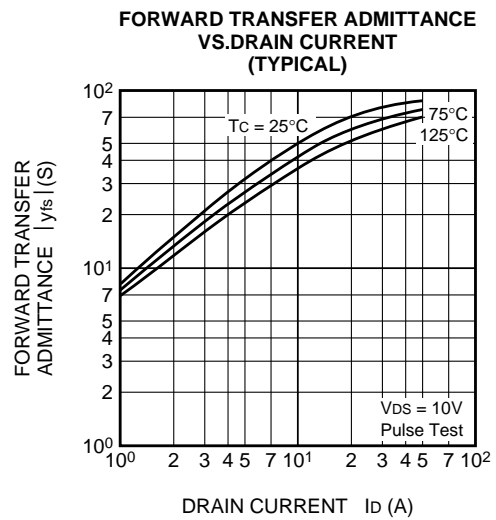
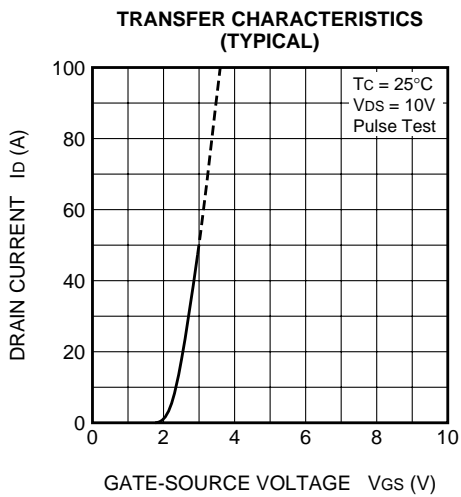
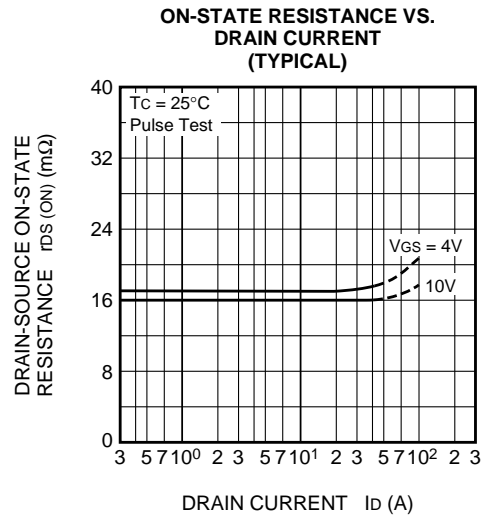
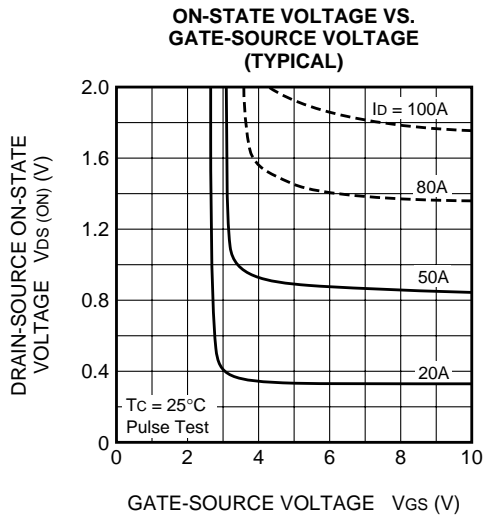


OUTPUT CHARACTERISTICS (TYPICAL)

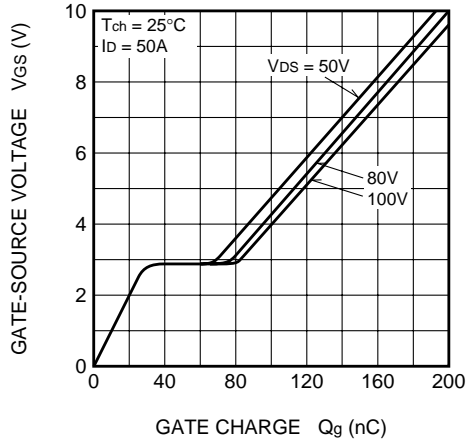


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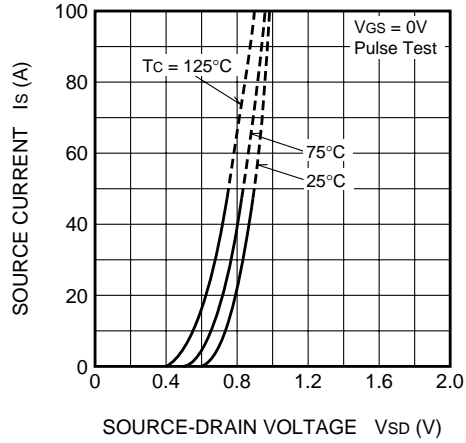




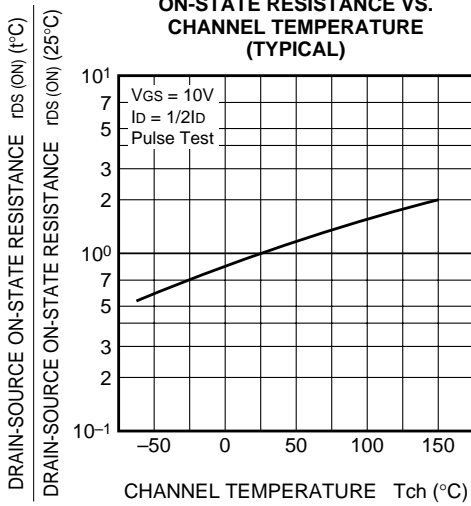
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



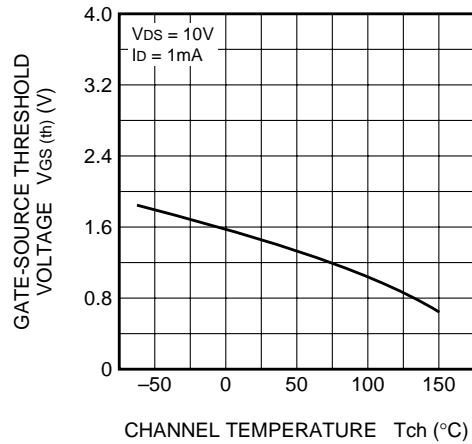
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



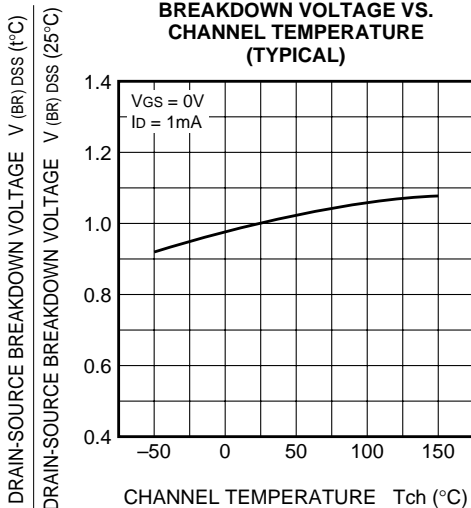
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

